BOURNS®

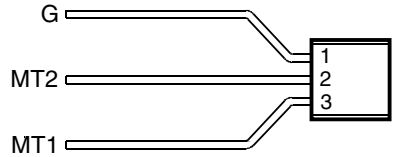
- **1.5 A RMS**
- **Glass Passivated Wafer**
- **400 V to 600 V Off-State Voltage**
- **Max I_{GT} of 10 mA**
- **Package Options**

PACKAGE	PACKING	PART # SUFFIX
LP	Bulk	(None)
LP with fomed leads	Tape and Reel	R

LP PACKAGE
(TOP VIEW)

MDC2AA

LP PACKAGE
WITH FORMED LEADS
(TOP VIEW)



MDC2AB

absolute maximum ratings over operating case temperature (unless otherwise noted)

RATING		SYMBOL	VALUE	UNIT
Repetitive peak off-state voltage (see Note 1)	TICP206D TICP206M	V_{DRM}	400 600	V
Full-cycle RMS on-state current at (or below) 85°C case temperature (see Note 2)		$I_{T(RMS)}$	1.5	A
Peak on-state surge current full-sine-wave at (or below) 25°C case temperature (see Note 3)		I_{TSM}	10	A
Peak on-state surge current half-sine-wave at (or below) 25°C case temperature (see Note 4)		I_{TSM}	12	A
Peak gate current		I_{GM}	±0.2	A
Average gate power dissipation at (or below) 85°C case temperature (see Note 5)		$P_{G(AV)}$	0.3	W
Operating case temperature range		T_C	-40 to +110	°C
Storage temperature range		T_{stg}	-40 to +125	°C
Lead temperature 1.6 mm from case for 10 seconds		T_L	230	°C

NOTES: 1. These values apply bidirectionally for any value of resistance between the gate and Main Terminal 1.
2. This value applies for 50-Hz full-sine-wave operation with resistive load. Above 85°C derate linearly to 110°C case temperature at the rate of 60 mA/°C.
3. This value applies for one 50-Hz full-sine-wave when the device is operating at (or below) the rated value of on-state current. Surge may be repeated after the device has returned to original thermal equilibrium. During the surge, gate control may be lost.
4. This value applies for one 50-Hz half-sine-wave when the device is operating at (or below) the rated value of on-state current. Surge may be repeated after the device has returned to original thermal equilibrium. During the surge, gate control may be lost.
5. This value applies for a maximum averaging time of 20 ms.

electrical characteristics at 25°C case temperature (unless otherwise noted)

PARAMETER		TEST CONDITIONS			MIN	TYP	MAX	UNIT
I_{DRM}	Repetitive peak off-state current	V_D = rated V_{DRM}	I_G = 0				±20	µA
I_{GT}	Gate trigger current	V_{supply} = +12 V†	R_L = 10 Ω	$t_{p(g)}$ > 20 µs			8	mA
		V_{supply} = +12 V†	R_L = 10 Ω	$t_{p(g)}$ > 20 µs			-8	
		V_{supply} = -12 V†	R_L = 10 Ω	$t_{p(g)}$ > 20 µs			-8	
		V_{supply} = -12 V†	R_L = 10 Ω	$t_{p(g)}$ > 20 µs			10	
V_{GT}	Gate trigger voltage	V_{supply} = +12 V†	R_L = 10 Ω	$t_{p(g)}$ > 20 µs			2.5	V
		V_{supply} = +12 V†	R_L = 10 Ω	$t_{p(g)}$ > 20 µs			-2.5	
		V_{supply} = -12 V†	R_L = 10 Ω	$t_{p(g)}$ > 20 µs			-2.5	
		V_{supply} = -12 V†	R_L = 10 Ω	$t_{p(g)}$ > 20 µs			2.5	

† All voltages are with respect to Main Terminal 1.

electrical characteristics at 25°C case temperature (unless otherwise noted) (continued)

PARAMETER		TEST CONDITIONS			MIN	TYP	MAX	UNIT
V_T	On-state voltage	I_T = ±1 A	I_G = 50 mA	(see Note 6)			±2.2	V
I_H	Holding current	V_{supply} = +12 V†	I_G = 0	Init' I_{TM} = 100 mA			30	mA
		V_{supply} = -12 V†	I_G = 0	Init' I_{TM} = -100 mA			-30	
I_L	Latching current	V_{supply} = +12 V†	(see Note 7)				40	mA
		V_{supply} = -12 V†					-40	

† All voltages are with respect to Main Terminal 1.

NOTES: 6. This parameter must be measured using pulse techniques, t_p = ≤ 1 ms, duty cycle ≤ 2 %. Voltage-sensing contacts separate from the current carrying contacts are located within 3.2 mm from the device body.

7. The triacs are triggered by a 15-V (open circuit amplitude) pulse supplied by a generator with the following characteristics: R_G = 100 Ω, $t_{p(g)}$ = 20 µs, t_r = ≤ 15 ns, f = 1 kHz.

TYPICAL CHARACTERISTICS

GATE TRIGGER CURRENT vs TEMPERATURE

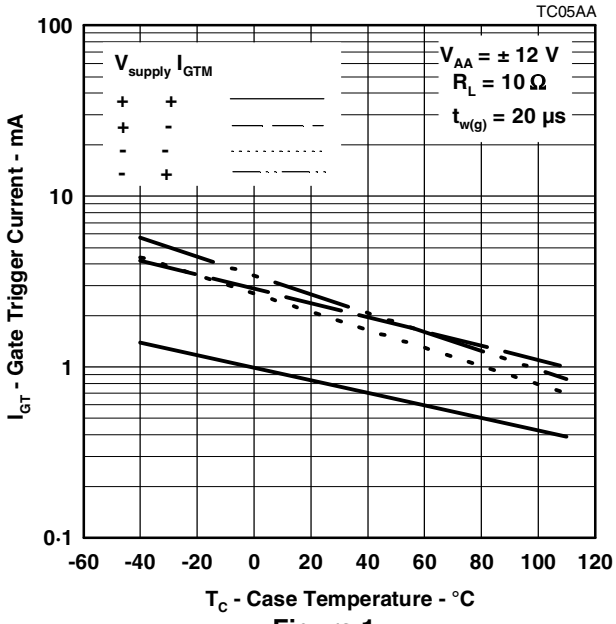


Figure 1.

GATE TRIGGER VOLTAGE vs TEMPERATURE

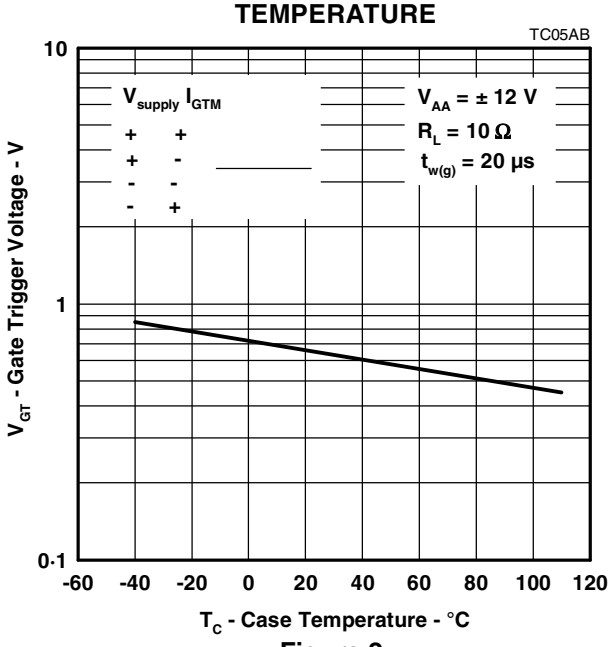


Figure 2.

TYPICAL CHARACTERISTICS

HOLDING CURRENT
vs
CASE TEMPERATURE

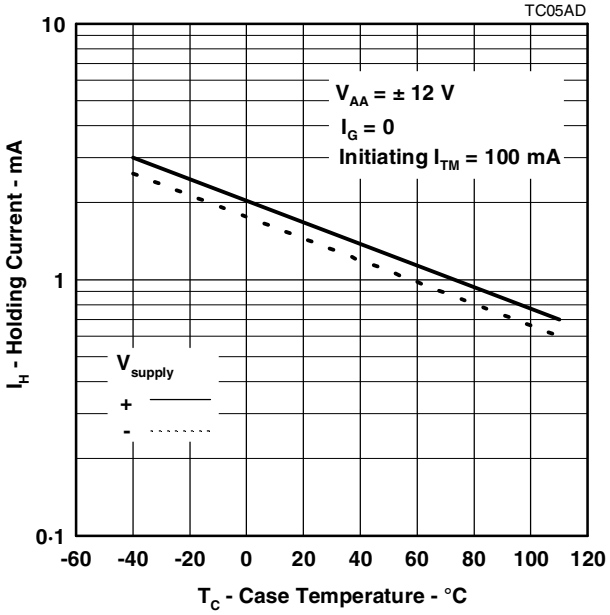


Figure 3.

LATCHING CURRENT
vs
CASE TEMPERATURE

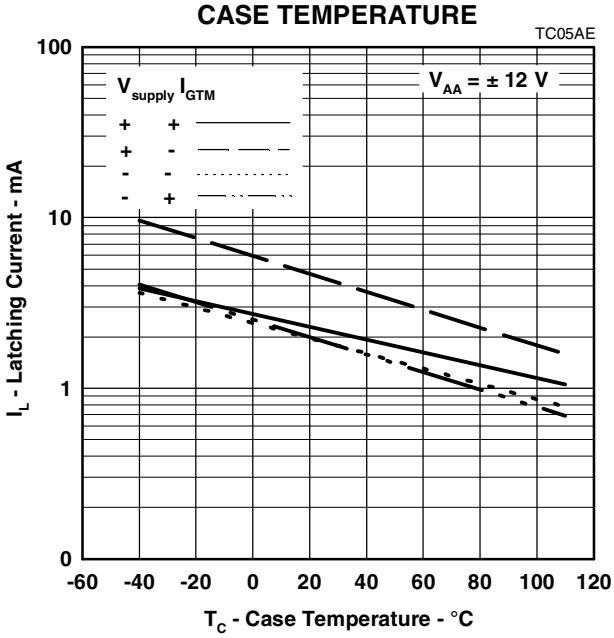


Figure 4.